## Pull-in of an RFMEMS Switch

## Introduction

This model analyzes an RF MEMS switch consisting of a thin micromechanical bridge suspended over a dielectric layer. A DC voltage greater than the pull-in voltage is applied across the switch, causing the bridge to collapse onto the dielectric layer with a resulting increase in the capacitance of the device. A penalty based contact force is implemented to model the contact forces as the bridge comes into contact with the dielectric.

## Model Definition

Figure 1 shows the device geometry. The switch consists of a square polysilicon plate suspended $0.9 \mu \mathrm{~m}$ above a $0.1 \mu \mathrm{~m}$ thick thin film of Silicon Nitride (relative dielectric constant 7.5). Beneath the substrate is a silicon counter-electrode that is grounded. The plate is structurally anchored to the substrate by four rectangular flexures at its corners but is electrically isolated from it. Initially a small potential of just 1 mV is applied to the polysilicon. This voltage is sufficient to measure the DC capacitance of the device. After 25 $\mu \mathrm{s}$ the applied voltage is increased by 5 V with a step function that has a rise time of $10 \mu \mathrm{~s}$. The applied voltage is greater than the pull-in voltage of the structure and the switch pulls down onto the nitride. This process results in an abrupt and significant change in the capacitance of the device. Due to the symmetry of the device, it is possible to model only a single quadrant of the structure. The electromechanics interface explicitly meshes the gap between the polysilicon and the nitride. Since it is not possible to collapse the mesh to zero thickness the mesh is compressed into the nitride layer as the structure deforms. The nitride layer itself is consequently not represented explicitly within the geometry, but instead is represented by means of a spatially varying function for the dielectric constant within the gap. The dielectric constant in the gap is represented by a smoothed step function. The mid point of the step is chosen to be slightly above the height of the dielectric, so that when the polysilicon is in contact with the nitride the dielectric constant in the gap takes the value of the nitride dielectric constant for throughout the gap.


Figure 1: Top: Device geometry showing anchor points and symmetry planes. Bottom: Model geometry. Due to symmetry only one quadrant of the device needs to be modeled.

The contact between the polysilicon and the nitride is handled by an approximate penalty or barrier method, as described in Ref. 1. Stiff, nonlinear springs are used to represent the surface of the nitride. When the polysilicon is away from the nitride surface these springs have low stiffness and consequently have a negligible influence on the deformation. As the gap is reduced and approaches a predefined distance the spring becomes much stiffer and resists further closure. The contact forces $F_{C}$ are given by:

$$
\begin{gathered}
F_{c}=t_{n}-e_{n} g \\
F=t_{c}+\exp \binom{e_{n}}{t_{n}} \quad g \geq 0
\end{gathered}
$$

where $t_{\mathrm{n}}$ is the input estimate of the contact force, $e_{n}$ is the penalty stiffness, $g$ is the gap, that is, the distance between the polysilicon and the nitride. Note that when this method
is employed it is important to correctly tune the elastic stiffness and the contact force. The technique is an approximate one and does not correctly reproduce the details of the dynamics of contact. However the model is primarily concerned with estimating the time the switch takes to make contact and with computing the initial and final capacitance of the switch.

## TODO

1. What are the basic mechanism of the approximate penalty or barrier method.
2. Why was this specific contact force hosen?

## Results and Discussion

Figure 2 shows the spatial dependence of the total displacement when the device is pulled in. Most of the structure is in contact with the nitride and the bending occurs primarily in the flexures and in the vicinity of their attachment points. The form of the contact pressure, shown in Figure 3, is consistent with this observation and it is interesting to note that the largest forces occur in the vicinity of the flexures.

Time $=5 \mathrm{E}-5 \mathrm{~s}$ Surface: Total displacement ( $\mu \mathrm{m}$ )


Figure 2: Displacement of the polysilicon when pulled in. Most of the polysilicon structure is in contact with the silicon nitride with a displacement of $0.9 \mu \mathrm{~m}$.


Figure 3: Contact forces acting on the polysilicon when the structure is pulled in.
Figure 4 shows the displacement of the switch as a function of time. The switch takes significantly longer to close than the timescale on which the voltage changes, primarily due to its inertia. Figure 5 shows the capacitance of the device as a function of time. The capacitance increases by a factor of approximately 55 . Note that the capacitance changes on a significantly shorter timescale than the displacement.


Figure 4: Displacement of the center of the device as a function of time.


Figure 5: Capacitance of the device as a function of time. The transients in this plot that occur after the point of contact are not physical. The capacitance of the structure changes from 0.1 pF to 1.5 pF as a result of the pull-in.

## Reference

1. Crisfield M. A., Non-linear Finite Element Analysis of Solids and Structures, volume 2: Advanced Topics, John Wiley \& Sons Ltd., England, 1997.

Application Library path: MEMS_Module/Actuators/rf_mems_switch

## Modeling Instructions

From the File menu, choose New.

NE W
In the New window, click Model Wizard.

## MODEL WIZARD

1 In the Model Wizard window, click 3D.
2 In the Select Physics tree, select Structural Mechanics>Electromechanics (emi).
3 Click Add.
4 Click Study.
5 In the Select Study tree, select Preset Studies>Stationary.
6 Click Done.

## GEOMETRY1

1 In the Model Builder window, under Component 1 (comp1) click Geometry 1.
2 In the Settings window for Geometry, locate the Units section.
3 From the Length unit list, choose $\mu \mathrm{m}$.

## GLOBALDEFINITIONS

## Parameters

1 On the Home toolbar, click Parameters.
2 In the Settings window for Parameters, locate the Parameters section.

3 In the table, enter the following settings:

| Name | Expression | Value | Description |
| :--- | :--- | :--- | :--- |
| V0 | $1[\mathrm{mV}]$ | 0.001 V | Initial voltage |
| Vstep | $5[\mathrm{~V}]$ | 5 V | Voltage step |
| insheight | $100[\mathrm{~nm}]$ | $1 \mathrm{E}-7 \mathrm{~m}$ | Insulator height |
| airheight | $900[\mathrm{~nm}]$ | $9 \mathrm{E}-7 \mathrm{~m}$ | Air height |
| en | $1 e 15[\mathrm{~Pa} / \mathrm{m}]$ | $1 \mathrm{E} 15 \mathrm{~N} / \mathrm{m}^{3}$ | Spring stiffness |
| tn | $5 \mathrm{e} 5[\mathrm{~Pa}]$ | 5 E 5 Pa | Contact force |

## DEFINITIONS

## Variables 1

1 On the Home toolbar, click Variables and choose Local Variables.
2 In the Settings window for Variables, locate the Variables section.
3 In the table, enter the following settings:

| Name | Expression | Unit | Description |
| :---: | :---: | :---: | :---: |
| gap | airheight+w | m |  |
| contactpressure | $\begin{aligned} & (\text { gap<=0 })^{*} \\ & \text { (tn-en* } \\ & \text { gap) }+(\text { gap> } \\ & 0)^{*} \text { tn* } \\ & \text { exp(-gap* } \\ & \text { en/tn) } \end{aligned}$ | $\mathrm{N} / \mathrm{m}^{2}$ |  |
| Va | $\begin{aligned} & \text { V0+Vstep* } \\ & \operatorname{step}^{2}(\mathrm{t} / \\ & 1[\mathrm{~s}]) \\ & \hline \end{aligned}$ | V |  |

TODO

1. Gap -> what does the " +w " represent and where does it come from?
2. Va -> where does the come from?
3. Va -> what does the bracket after "step2" mean (t/l[s])?

## GEOMETRY1

## Work Plane 1 (wp1)

1 On the Geometry toolbar, click Work Plane.
2 In the Settings window for Work Plane, click Show Work Plane.
Rectangle 1 (r1)
1 On the Work Plane toolbar, click Primitives and choose Rectangle.
2 In the Settings window for Rectangle, locate the Size and Shape section.

3 In the Width text field, type 110

4 In the Height text field, type 5.
4 Locate the Position section. In the xw text field, type -60.

## Rectangle 2 (r2)

1 On the Work Plane toolbar, click Primitives and choose Rectangle.
2 In the Settings window for Rectangle, locate the Size and Shape section.
3 In the Width text field, type 50.
4 In the Height text field, type 60.
5 Locate the Position section. In the yw text field, type -10.

## Rectangle 3 (r3)

1 On the Work Plane toolbar, click Primitives and choose Rectangle.
2 In the Settings window for Rectangle, locate the Size and Shape section.
3 In the Width text field, type 110.
4 In the Height text field, type 60.
5 Locate the Position section. In the xw text field, type - 60 .
6 In the yw text field, type -10.

## Rectangle 4 (r4)

1 On the Work Plane toolbar, click Primitives and choose Rectangle.
2 In the Settings window for Rectangle, locate the Size and Shape section.
3 In the Width text field, type 110.
4 In the Height text field, type 10.
5 Locate the Position section. In the xw text field, type -60.
6 In the yw text field, type -2.5.
7 In the Model Builder window, click Geometry 1.

## Extrude 1 (ext1)

1 On the Geometry toolbar, click Extrude.
2 In the Settings window for Extrude, locate the Distances from Plane section.
3 In the table, enter the following settings:

[^0]
## Form Union (fin)

1 Right-click Extrude 1 (ext1) and choose Build Selected.
2 On the Geometry toolbar, click Build AII.
3 Click the Wireframe Rendering button on the Graphics toolbar.

## DEFINITIONS

TODO:
What are the definitions used for?
Step 1 (step1)
1 On the Home toolbar, click Functions and choose Local>Step.
2 In the Settings window for Step, locate the Parameters section.
3 In the Location text field, type 1.05 *insheight.
4 Click to expand the Smoothing section. In the Size of transition zone text field, type $0.05 *$ insheight.

## Step 2 (step2)

1 On the Home toolbar, click Functions and choose Local>Step.
2 In the Settings window for Step, locate the Parameters section.
3 In the Location text field, type $3 \mathrm{e}-5$.
4 Click to expand the Smoothing section. In the Size of transition zone text field, type 1e-5. Define selections.

## Explicit 1

1 On the Definitions toolbar, click Explicit.
2 In the Model Builder window, right-click Explicit 1 and choose Rename.
3 In the Rename Explicit dialog box, type Bridge in the New label text field.
4 Click OK.
5 Select Domains 8, 23, 26, and 29 only.

## Box 1

1 On the Definitions toolbar, click Box.
2 In the Model Builder window, right-click Box 1 and choose Rename.
3 In the Rename Box dialog box, type Gap in the New label text field.
4 Click OK.
5 In the Settings window for Box, locate the Box Limits section.
6 In the $\mathbf{z}$ maximum text field, type 1.1.

7 Locate the Output Entities section. From the Include entity if list, choose Entity inside box.

## Adjacent 1

1 On the Definitions toolbar, click Adjacent.
2 In the Model Builder window, right-click Adjacent 1 and choose Rename.
3 In the Rename Adjacent dialog box, type Bridge surface in the New label text field.
4 Click OK.
5 In the Settings window for Adjacent, locate the Input Entities section.
6 Under Input selections, click Add.
7 In the Add dialog box, select Bridge in the Input selections list.
8 Click OK.

## Box 2

1 On the Definitions toolbar, click Box.
2 In the Model Builder window, right-click Box 2 and choose Rename.
3 In the Rename Box dialog box, type Base in the New label text field.

## 4 Click OK.

5 In the Settings window for Box, locate the Geometric Entity Level section.
6 From the Level list, choose Boundary.
7 Locate the Box Limits section. In the $\mathbf{z}$ maximum text field, type 0.1 .
8 Locate the Output Entities section. From the Include entity if list, choose Entity inside box.

## Box 3

1 On the Definitions toolbar, click Box.
2 In the Settings window for Box, locate the Geometric Entity Level section.
3 From the Level list, choose Boundary.
4 Locate the Box Limits section. In the $\mathbf{z}$ minimum text field, type 0.9 .
5 In the $\mathbf{z}$ maximum text field, type 1.1.
6 Locate the Output Entities section. From the Include entity if list, choose Entity inside box.

## Intersection 1

1 On the Definitions toolbar, click Intersection.
2 In the Model Builder window, right-click Intersection 1 and choose Rename.

3 In the Rename Intersection dialog box, type Bridge lower side in the New label text field.

4 Click OK.
5 In the Settings window for Intersection, locate the Geometric Entity Level section.
6 From the Level list, choose Boundary.
7 Locate the Input Entities section. Under Selections to intersect, click Add.
8 In the Add dialog box, In the Selections to intersect list, choose Bridge surface and Box 3.
9 Click OK.

## Box 4

1 On the Definitions toolbar, click Box.
2 In the Model Builder window, right-click Box 4 and choose Rename.
3 In the Rename Box dialog box, type Symmetry x in the New label text field.
4 Click OK.
5 In the Settings window for Box, locate the Geometric Entity Level section.
6 From the Level list, choose Boundary.
7 Locate the Box Limits section. In the $\mathbf{x}$ minimum text field, type 45 .
8 Locate the Output Entities section. From the Include entity if list, choose Entity inside box.

## Box 5

1 On the Definitions toolbar, click Box.
2 In the Model Builder window, right-click Box 5 and choose Rename.
3 In the Rename Box dialog box, type Symmetry y in the New label text field.
4 Click OK.
5 In the Settings window for Box, locate the Geometric Entity Level section.
6 From the Level list, choose Boundary.
7 Locate the Box Limits section. In the y minimum text field, type 45.
8 Locate the Output Entities section. From the Include entity if list, choose Entity inside box.

Load the materials.

## ADD MATERIAL

1 On the Home toolbar, click Add Material to open the Add Material window.

2 Go to the Add Material window.
3 In the tree, select Built-In>Air.
4 Click Add to Component in the window toolbar.

## ADD MATERIAL

1 Go to the Add Material window.
2 In the tree, select MEMS>Semiconductors>Si-Polycrystalline Silicon.
3 Click Add to Component in the window toolbar.
4 On the Home toolbar, click Add Material to close the Add Material window.

MATERIALS

## Si - Polycrystalline Silicon (mat2)

1 In the Model Builder window, under Component 1 (comp1)>Materials click $\mathbf{S i}$ - Polycrystalline Silicon (mat2).

2 In the Settings window for Material, locate the Geometric Entity Selection section.
3 From the Selection list, choose Bridge.

## Material 3 (mat3)

1 In the Model Builder window, under Component 1 (comp1) right-click Materials and choose Blank Material.

2 In the Settings window for Material, locate the Geometric Entity Selection section.
3 From the Selection list, choose Gap.
4 Click to expand the Material properties section. Locate the Material Properties section. From the Material type list, choose Nonsolid.

5 Locate the Material Contents section. In the table, enter the following settings:

| Property | Name | Value | Unit | Property <br> group |
| :--- | :--- | :--- | :--- | :--- |
| Relative permittivity | epsilonr | 7.5 -step1 1 <br> $(\mathrm{z}) * 6.5$  |  | Basic |

## ELECTROMECHANICS (EMI)

## Linear Elastic Material 1

1 On the Physics toolbar, click Domains and choose Linear Elastic Material.
2 In the Settings window for Linear Elastic Material, locate the Domain Selection section.
3 From the Selection list, choose Bridge.

## Fixed Constraint 1

1 On the Physics toolbar, click Boundaries and choose Fixed Constraint.
2 Select Boundary 24 only.

## Symmetry 1

1 On the Physics toolbar, click Boundaries and choose Symmetry.
2 In the Settings window for Symmetry, locate the Boundary Selection section.
3 From the Selection list, choose Symmetry x.

## Symmetry 2

1 On the Physics toolbar, click Boundaries and choose Symmetry.
2 In the Settings window for Symmetry, locate the Boundary Selection section.
3 From the Selection list, choose Symmetry y.

## Boundary Load 1

1 On the Physics toolbar, click Boundaries and choose Boundary Load.
2 Select Boundaries 26, 79, 89, and 99 only.
3 In the Settings window for Boundary Load, locate the Force section.
4 Specify the $\mathbf{F}_{\mathrm{A}}$ vector as

| 0 | x |
| :--- | :--- |
| 0 | y |
| contactpressure | z |

TODO:

1. Why does the z-component of the boundary force has the value "contactpressure"

## Prescribed Mesh Displacement 2

1 On the Physics toolbar, click Boundaries and choose Prescribed Mesh Displacement.
2 In the Settings window for Prescribed Mesh Displacement, locate the Boundary Selection section.

3 From the Selection list, choose Symmetry x.
4 Locate the Prescribed Mesh Displacement section. Clear the Prescribed y displacement check box.

5 Clear the Prescribed z displacement check box.

## Prescribed Mesh Displacement 3

1 On the Physics toolbar, click Boundaries and choose Prescribed Mesh Displacement.
2 In the Settings window for Prescribed Mesh Displacement, locate the Boundary Selection section.

3 From the Selection list, choose Symmetry y.
4 Locate the Prescribed Mesh Displacement section. Clear the Prescribed $\mathbf{x}$ displacement check box.

5 Clear the Prescribed z displacement check box.

## Terminal 1

1 On the Physics toolbar, click Boundaries and choose
Terminal. Define the voltage applied to the bridge lower side.
2 In the Settings window for Terminal, locate the Boundary Selection section.
3 From the Selection list, choose Bridge surface.
4 Locate the Terminal section. From the Terminal type list, choose Voltage.
5 In the $V_{0}$ text field, type Va.

## Terminal 2

1 On the Physics toolbar, click Boundaries and choose Terminal. Define the voltage applied to the base.

2 In the Settings window for Terminal, locate the Boundary Selection section.
3 From the Selection list, choose Base.
4 Locate the Terminal section. From the Terminal type list, choose Voltage.
5 In the $V_{0}$ text field, type 0 .

## Terminal 3

1 On the Physics toolbar, click Boundaries and choose Terminal.
Add another Terminal to the bridge lower side. This terminal is used for the first (Stationary) study step. It will be disabled in the transient step which will make Terminal 1 active.
TODO:

1. Why is terminal3 needed and what it is used for ?

2 In the Settings window for Terminal, locate the Boundary Selection section.
3 From the Selection list, choose Bridge surface.
4 Locate the Terminal section. From the Terminal type list, choose Voltage.
5 In the $V_{0}$ text field, type V0.

MESH1

In the Model Builder window, under Component 1 (comp1) right-click Mesh 1 and choose More Operations>Mapped.

## Mapped 1

1 Select Boundaries 10,20,30,40,50,63,73, 83, 93, and 103 only.
2 In the Model Builder window, right-click Mesh 1 and choose Swept.

## Swept 1

In the Model Builder window, under Component 1 (comp1)>Mesh 1 right-click Swept 1 and choose Distribution.

## Distribution 1

1 In the Settings window for Distribution, locate the Domain Selection section.
2 From the Selection list, choose Gap.
3 Locate the Distribution section. In the Number of elements text field, type 8.

## 4 Click Build AII.

Define the study steps. The first step (Stationary) is used to define the initial conditions of the transient problem (Step 2).

## STUDY1

## 1. Step2: What is the aim of this step? <br> 2. Step2: Why do we have to disable terminal 3 <br> 3. Step2: Why do we have to change the default solver? <br> Time Dependent <br> On the Study toolbar, click Study Steps and choose Time Dependent>Time Dependent.

## Step 2: Time Dependent

1 In the Settings window for Time Dependent, locate the Study Settings section.
2 In the Times text field, type range( $0,5 \mathrm{e}-7,5 \mathrm{e}-5$ ).
3 Locate the Physics and Variables Selection section. Select the Modify physics tree and variables for study step check box.
4 In the Physics and variables selection tree, select Component 1 (comp1)>Electromechanics (emi)>Terminal 3.

## 5 Click Disable.

Change the default solver to a Fully CoupledDirect solver and use BDF time stepping.

## TODO: Why do we have to change the default settings to BDF time stepping and Fully Coupled Direct?

## Solution 1 (sol1)

TODO: What is time stepping ? and what is used for ?
1 On the Study toolbar, click Show Default Solver.
2 In the Model Builder window, expand the Solution 1 (sol1) node, then click Time-Dependent Solver 1.

3 In the Settings window for Time-Dependent Solver, click to expand the Time stepping section.

5 Locate the Time Stepping section. From the Method list, choose BDF
6 From the Steps taken by solver list, choose Intermediate.
TODO: What does it mean to set the steps to intermediate ?

7 Right-click Study 1>Solver Configurations>Solution 1 (sol1)>Time-Dependent Solver 1 and choose Fully Coupled.
Todo: Why do we have to set the time dependent solver 1 to "fully coupled"? What is it doing?

8 In the Settings window for Fully Coupled, click to expand the Method and termination section.
TODO: What is the "method and termination section" used for ?
9 Locate the Method and Termination section. From the Nonlinear method list, choose Automatic (Newton).
TODO: Why was the "Automatic(Netwon)" chosen ? What is it doing?
10In the Model Builder window, under Study 1>Solver Configurations>Solution 1 (sol1)> Time-Dependent Solver 1 right-click Direct and choose Enable.
TODO: Why do we have to "enable" the Direct solver ? What is its use ?
11 In the Settings window for Direct, locate the General section.
12From the Solver list, choose PARDISO.
TODO: What is the "PARDISO" and what is it used for ?
Why do we need this solver in this specific application?
13Click Compute.
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    4

